

(19)
(12)

(KR)
(A)

(51) 。 Int. Cl. ⁷
H05B 33/10

(11)
(43)

2002 - 0072063
2002 09 14

(21)
(22)

10 - 2001 - 0012032
2001 03 08

(71)

455 - 6

(72)

1029 1 101 - 404

353 - 1403

108 - 1104

11 - 1 522

(74)

:

(54)

ITO(indium tin oxide)

(a)

(b)

ITO

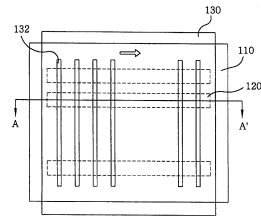
(c) ITO

(d)

(e)

(c) (d)

【도 5c】



1 ,

2 DBR ,

3 CCF ,

4 W - CFF ,

5a 5c ,

6a 6d 5c 5c A - A '

< >

110 : 120 : ITO

130 : 132 :

140 :

160, 170, 180 : , ,

가
가 , , 가 (LCD), (PDP),
(VFD), (Electroluminescence : EL)
가 (Electroluminesc
e : EL)
(individual pixel type) , DBR
CCF , W - CFF
1 (10) (shadow mask)() 가 가
(R - , G - , B - OELD) (22, 24, 26)
(22, 24, 26)
가
- (ink - jet) 가
(10) 가
2 DBR (R), (G) (B)
DBR(Distributed Brag Reflector)(32, 34, 36) (10)
(Broad Band OELD)(42, 44, 46) DBR(32, 34, 36)
3 CCF 가
(10) ITO (52, 54, 56) (CCF : Color Converting
g Film)(52, 54, 56) (Blue - OELD)(62, 64,
66) CCF
LCD (CFF : Color Filter Film) 가 (cross - talk)
가 가
가
4 LCD W - CFF (10)
CFF(72, 74, 76) (White - OELD)(82, 84, 86)
가

indium tin oxide) ; (a) ITO(indium tin oxide) ; (b) ITO ; (c) ITO ; (d) ; (e) (c) (d) (c) .

5 .
 5a 0.7mm (110) , 가 1000 ITO(indium tin oxide)가 (120) t1 (+) ITO (120) .
 5b (110) 150 - 200 μ m (130) 가 , 가 1 (132) (110) ITO(120) (130) , t2 (132) μ m , t3 (132) .

¹
 $t2^2 < t3 \leq t2^5$

, t3 , t3 t2 2 (t2*2) , , t3 t2 5 (t2*5) , (t2) .
 5c 6a , ITO (120) (110) (130) (140) (150) AL:Li (140) 3000 , (-) .

6b ITO (120) (140) , (160)
 (140)
 (hall injection layer)(142), (hall transfer layer)(144),
 (emission layer)(146), (electron layer)(148)
 (146) , (146)
 (146) , (R)

iton) , ITO (120) (150) (+) (-) , ITO (120) (exc
 , 가 (140)
 , ITO (120) (ground state)
 , (160) , ITO (110) (130) t3
 (160) , 5c (146)
 (150)
 (160) (170)
 (6c).

ITO (110) (130) t3
 (170) , 5c (146)
 (150)
 (170) (180) , , (160, 170, 180) (130) t3
 (200)

ITO (110) (130) ITO (110)
 (130) ITO (110) () t3
 () PZT
 PZT nm

(200) (144) ITO (120) (150) 가 (146)

가 .

(57)

1.

(a) ITO(indium tin oxide) ;

(b) ITO ;

(c) ITO ;

(d) ;

(e) (c) (d) ,

2.

1 , (t3) ,

$$t2*2 < t3 \leq t2*5$$

, t2 , t3 .

3.

1 2 , (hall i
njection layer), (electron layer) , (hall transfer layer), (emission layer),

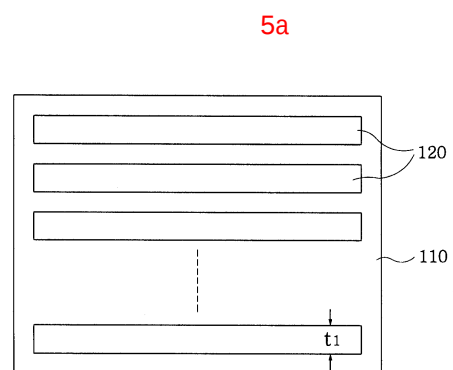
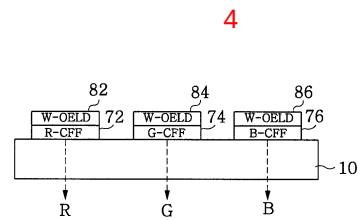
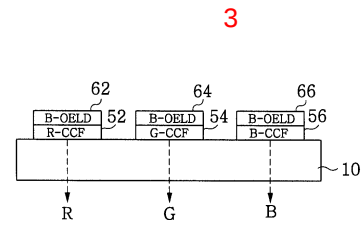
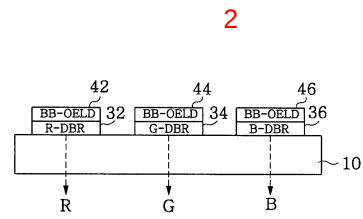
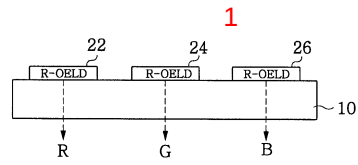
(c) ,

4.

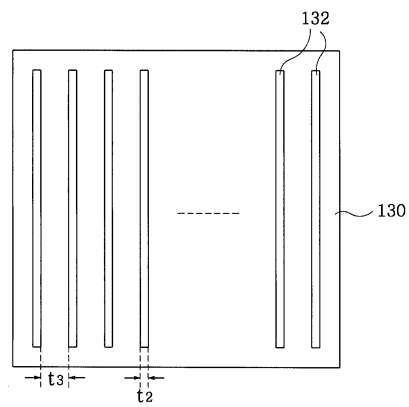
1 , Al:Li .

5.

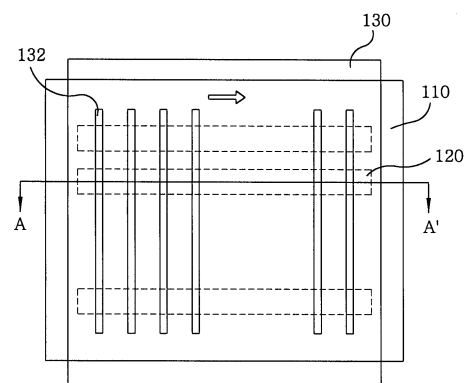
1 , (t3)



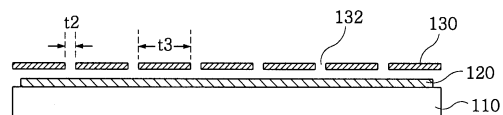
5b



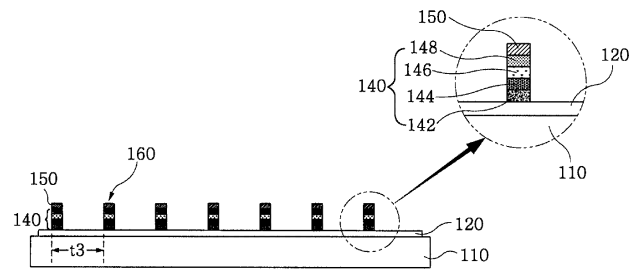
5c



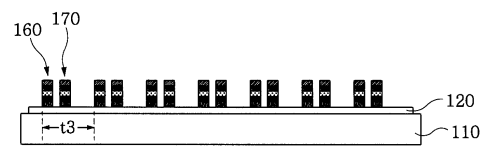
6a



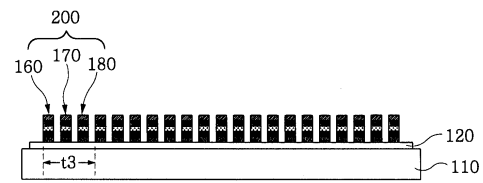
6b



6c



6d



专利名称(译)	使用单分子有机电致发光材料制造全色显示系统的方法		
公开(公告)号	KR1020020072063A	公开(公告)日	2002-09-14
申请号	KR1020010012032	申请日	2001-03-08
[标]申请(专利权)人(译)	电子部品研究院		
申请(专利权)人(译)	韩国电子技术研究所		
当前申请(专利权)人(译)	韩国电子技术研究所		
[标]发明人	PARK KWANG BUM 박광범 MOON HYUN CHAN 문현찬 CHOI SEONG HO 최성호 KIM IN HOE 김인회		
发明人	박광범 문현찬 최성호 김인회		
IPC分类号	H05B33/10		
CPC分类号	H01L27/3211 H01L51/001 H01L51/0011 H01L51/56		
代理人(译)	张居正, KU SEONG		
其他公开文献	KR100378065B1		
外部链接	Espacenet		

摘要(译)

本发明涉及使用单分子有机电致发光材料制造全色显示系统的方法，并包括形成全彩色显示器有机电致发光器件的步骤，它移动到所形成的单色有机电致发光中的相邻位置。如上所述的像素区域在狭缝(e)之间的距离内，金属掩模，单色有机电致发光像素区域形成ITO(氧化铟锡)电极，其具有(a)玻璃基板，在纵向方向上，矩形类型被图案化，之后金属部分从(b)金属板上移除到玻璃基板上的ITO电极和正交方向上，并且多个长切口在其形成的玻璃基板上具有切口的金属掩模，并以此方式制造金属掩模，并且其中(c)形成ITO电极，用于单色辐射的单体有机发光材料是沉积的d用热蒸发法将金属混合物热层压在(d)单体有机发光材料层上，形成金属电极。

